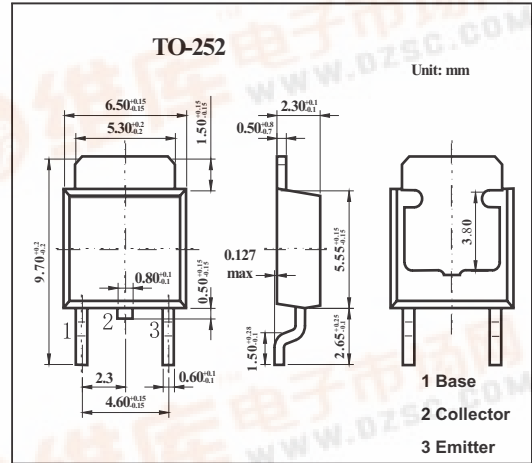


SMD Type Transistors

PNP Epitaxial Planar Silicon Transistor
2SA1773

■ Features

- High breakdown voltage
- Large current capacity (Ic=2A)

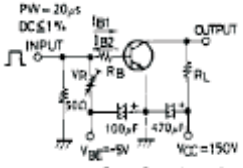


■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	-400	V
Collector to Emitter Voltage	V _{CE0}	-400	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _c	-2	A
Collector Current (Pulse)	I _c	-4	A
Collector Dissipation	P _c	1	W
T _c =25°C		15	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

2SA1773

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-300\text{V}, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.1	μA
DC Current Gain*	h_{FE}	$V_{CE}=-10\text{V}, I_C=-100\text{mA}$	40		200	
Gain- Bandwidth Product	f_T	$V_{CE}=-10\text{V}, I_C=-50\text{mA}$		40		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-400			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, R_{BE}=\infty$	-400			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Output Capacitance	C_{ob}	$V_{CB}=-30\text{V}, f=1\text{MHz}$		25		pF
Turn-ON Time	t_{on}	 <p> $PW=20\mu\text{s}$ $DC \leq 1\%$ $I_{B1} = -10I_{B2} = I_C = 500\text{mA}$ $R_C = 300\Omega, R_B = 20\Omega, \text{ at } I_C = 500\text{mA}$ (For PNP, the polarity is reversed.) </p>		0.12		μs
Storage Time	t_{stg}			3		
Fall Time	t_f			0.3		

■ h_{FE} Classification

Rank	C	D	E
h_{FE}	40 to 80	60 to 120	100 to 200